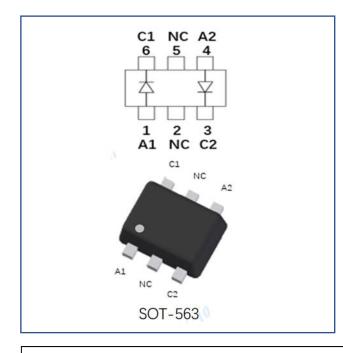






Schottky Barrier Diode



Features

Moisture sensitivity level 1

• Reverse voltage: 40V

Average forward current : 200mA

Application

• High frequency and low voltage rectifier

Mechanical data

• Package: SOT-563

• Terminals: Tin plated leads, solderable per

J-STD-002 and JESD22-B102

■ Maximum Ratings (Ta=25°C Unless otherwise specified)

ltem	Symbol	Unit	Value
Device marking code			KAN
Continuous reverse voltage	V _R	V	40
Forward continuous current	I _F	mA	200
Non-repetitive surge peak forward current @ t=8.3ms half-sine wave		٨	0.6
Non-repetitive surge peak forward current @ t=1ms square wave	- I _{FSM}	А	1.5
Power dissipation	P _D	mW	150
Junction temperature	TJ	°C	-55 to +125
Storage temperature	T _{STG}	°C	-55 to +150



BAS40V



■ Electrical Characteristics (T_a=25°C Unless otherwise specified)

Item	Symbol	Unit	Conditions	Min	Тур	Max
Reverse breakdown voltage	V _R	V	I _R =10uA	40		
Converse veltage	V _{F1}	V	I _F =1mA			0.38
Forward voltage	V _{F2}	V	I _F =40mA			1
Reverse current	I _R	nA	V _R =30V			200
Junction capacitance	Cj	pF	f=1.0MHz, V _R =0V			5
Reverse recovery time	Trr	ns	$I_F = I_R = 5 \text{mA}$, $I_T = 0.1 \text{*IR}$, $R_L = 100 \Omega$			5

■ Thermal Characteristics

Parameter	Symbol	Unit	Value
Thermal resistance, junction-to-ambient	R ₀ J-A ⁽¹⁾	°C/W	667
Thermal resistance, junction-to-case	RθJ-C ⁽¹⁾	°C/W	533

Note:

(1) Thermal resistance from junction to ambient and from junction to lead mounted on P.C.B. with 25.4mm*25.4mm copper pad areas





■Characteristics

Fig 1: P_D-Ta Curve

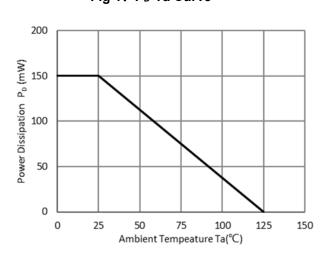


Fig 2: Capacitance Capability

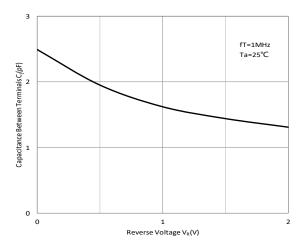


Fig 3: Typical Forward Characteristics

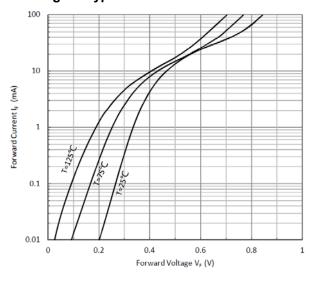
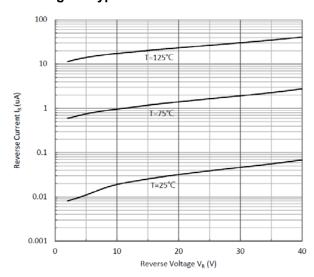


Fig 4: Typical Reverse Characteristics





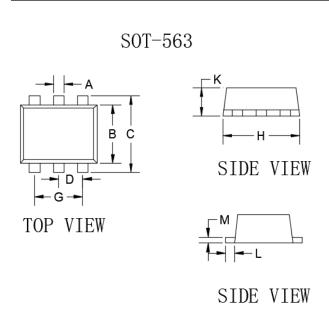




■Ordering Information

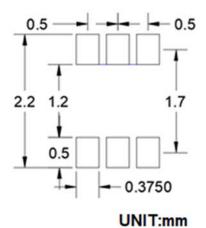
Preferred P/N	Packing code	Unit weight(g)	Minimum package(pcs)	Inner box quantity(pcs)	Outer carton quantity(pcs)	Delivery mode
BAS40V	F2	Approximate 0.0035	3000	30000	120000	7" reel

■ Outline Dimensions



DIMENSIONS					
DIM	INC	HES	ММ		
	MIN	MAX	MN	MAX	
А	0.006	0.011	0.150	0.300	
В	0.043	0.051	1.100	1.300	
С	0.059	0.067	1.500	1.700	
D	0.016	0.024	0.400	0.600	
G	0.035	0.043	0.900	1.100	
Н	0.059	0.067	1.500	1.700	
К	0.021	0.026	0.550	0.650	
L	0.004	0.011	0.100	0.300	
М	0.004	0.007	0.100	0.180	

■ Suggested Pad Layout





BAS40V



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